

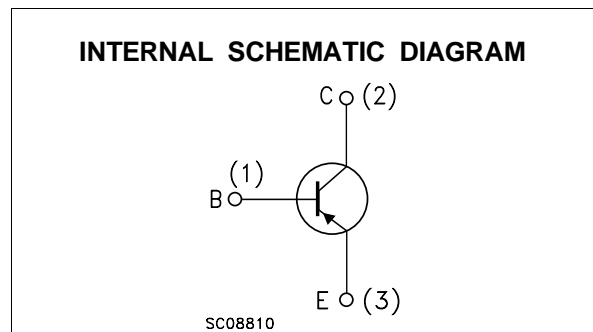
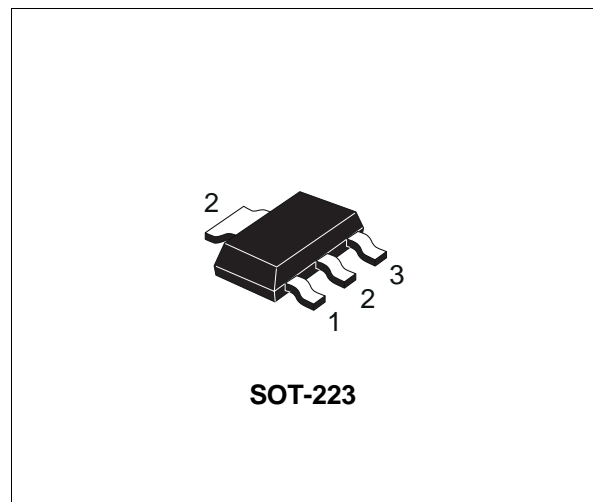
LOW POWER PNP TRANSISTOR

Ordering Code	Marking
BCP52-16	BCP5216

- SILICON EPITAXIAL PLANAR PNP MEDIUM VOLTAGE TRANSISTOR
- SOT-223 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- THE NPN COMPLEMENTARY TYPE IS BCP55-16

APPLICATIONS

- MEDIUM VOLTAGE LOAD SWITCH TRANSISTORS
- OUTPUT STAGE FOR AUDIO AMPLIFIERS CIRCUITS
- AUTOMOTIVE POST-VOLTAGE REGULATION



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	-60	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	-60	V
V_{CER}	Collector-Emitter Voltage ($R_{BE} = 1K\Omega$)	-60	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	-5	V
I_C	Collector Current	-1	A
I_{CM}	Collector Peak Current ($t_p < 5$ ms)	-1.5	A
I_B	Base Current	-0.1	A
I_{BM}	Base Peak Current ($t_p < 5$ ms)	-0.2	A
P_{tot}	Total Dissipation at $T_{amb} = 25$ °C	1.4	W
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

BCP52-16

THERMAL DATA

$R_{thj-amb}$ •	Thermal Resistance Junction-Ambient	Max	89.3	°C/W
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• Device mounted on a PCB area of 1 cm²

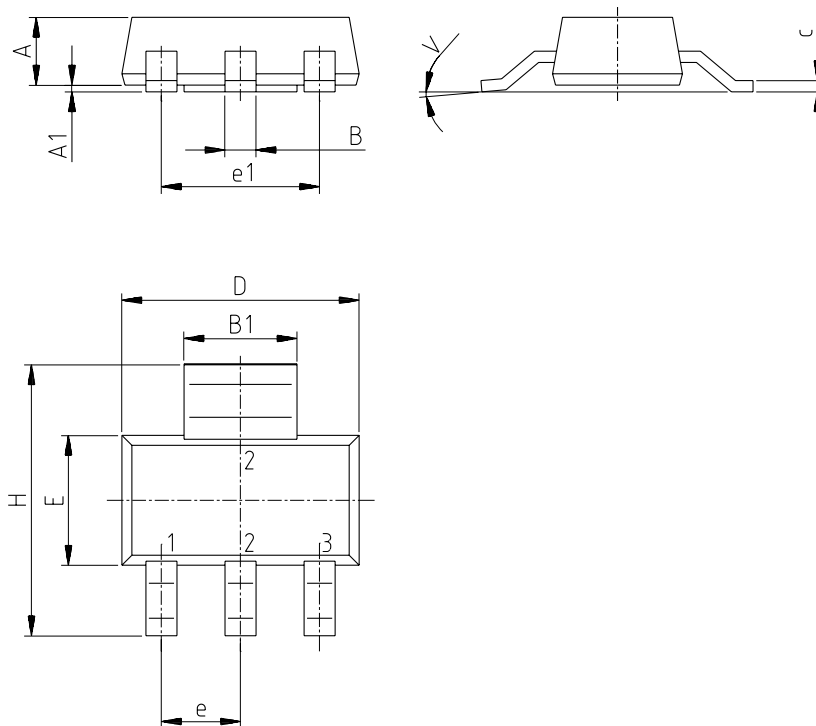
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current (I _E = 0)	V _{CB} = -30 V V _{CB} = -30 V T _j = 125 °C			-100 -10	nA μA
V _{(BR)CBO}	Collector-Base Breakdown Voltage (I _E = 0)	I _C = -100 μA	-60			V
V _{(BR)CEO} *	Collector-Emitter Breakdown Voltage (I _B = 0)	I _C = -20 mA	-60			V
V _{(BR)CER}	Collector-Emitter Breakdown Voltage (R _{BE} = 1 KΩ)	I _C = -100 μA	-60			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage (I _C = 0)	I _E = -10 μA	-5			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = -500 mA I _B = -50 mA			-0.5	V
V _{BE(on)} *	Base-Emitter On Voltage	I _C = -500 mA V _{CE} = -2 V			-1	V
h _{FE} *	DC Current Gain	I _C = -5 mA V _{CE} = -2 V I _C = -150 mA V _{CE} = -2 V I _C = -500 mA V _{CE} = -2 V	40 100 25		250	
f _T	Transition Frequency	I _C = -10 mA V _{CE} = -5 V f = 20 MHz		50		MHz

* Pulsed: Pulse duration = 300 μs, duty cycle ≤ 1.5 %

SOT-223 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.80			0.071
B	0.60	0.70	0.80	0.024	0.027	0.031
B1	2.90	3.00	3.10	0.114	0.118	0.122
c	0.24	0.26	0.32	0.009	0.010	0.013
D	6.30	6.50	6.70	0.248	0.256	0.264
e		2.30			0.090	
e1		4.60			0.181	
E	3.30	3.50	3.70	0.130	0.138	0.146
H	6.70	7.00	7.30	0.264	0.276	0.287
V			10°			10°
A1		0.02				



P008B

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